HE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No.09/536,037 Filing DateMarch 27, 2000 AssigneeMicron Technology, Inc. Group Art Unit2822 ExaminerToniae M. Thomas Attorney's Docket No.MI22-1398

Title: Low k Interlevel Dielectric Layer Fabrication Methods

To:

Box RCE

Commissioner for Patents

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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

This Request for Continued Examination (RCE) Application is being filed in an abundance of caution to ensure consideration of the references listed on the attached form PTO-1449.

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. No admission is made regarding whether the submitted references are prior art.

Respectfully submitted,

Dated: N Me

Reg. No. 44,854

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Form PTO-144	49		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1398			SERIAL NO. 09/536,037		
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*Examiner's Initials		Document Number	Date	Nan	ne	Class	Sub	class	Filing Date If Appropriate		
	AA	6,121,133	09/19/00	lyer et al.		438	636	6			
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	AJ	TW 47112 A	01/01/2002	Taiwan – Abstract			<u> </u>		х		
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)											
	АМ	Wolf, S., and Tauber, Richard, Silicon Processing for the VLSI Era; Vol. 1; Process Technology; "Silicon: Single Crystal Growth and Wafer Preparation"; pages 1 and 2									
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EXAMINER		DATE CONS	DATE CONSIDERED								
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in											

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